

# MOSFET - Power, Single N-Channel, Source Down, WDFN9

## 25 V, 0.85 mΩ, 264 A NTTFSS1D1N02P1E

### Features

- Advanced Source-Down Package Technology (3.3x3.3mm) with Excellent Thermal Conduction
- Ultra Low  $R_{DS(on)}$  to Improve System Efficiency
- Low  $Q_G$  and Capacitance to Minimize Driving and Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- DC-DC Switching Applications
- ORing Applications
- Power Load Switch
- Battery Management and Protection

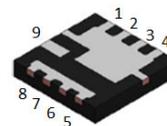
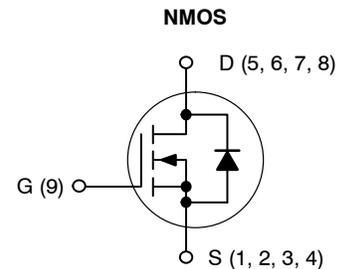
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	25	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 16$	V	
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	264	A
		$T_C = 85^\circ\text{C}$		189	
Power Dissipation $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$	89	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	39	A
		$T_A = 85^\circ\text{C}$		28	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	2	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$	900	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 63 \text{ A}, L = 0.1 \text{ mH}$ )		$E_{AS}$	173	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$	
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

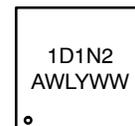
1. Surface-mounted on FR4 board using a 1 in<sup>2</sup> pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are valid for the particular conditions noted.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
25 V	0.85 mΩ @ 10 V	264 A
	1.05 mΩ @ 4.5 V	



WDFN9  
CASE 511EB

### MARKING DIAGRAM



1D1N2 = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTTFSS1D1N02P1E

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	1.4	$^{\circ}C/W$
Junction-to-Ambient – Steady State (Note 1, 2)	$R_{\theta JA}$	60	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V, I_D = 250 \mu A$	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250 \mu A, \text{ref to } 25^{\circ}C$		12.8		$mV/^{\circ}C$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0 V, V_{DS} = 20 V$	$T_J = 25^{\circ}C$		1.0	$\mu A$
			$T_J = 125^{\circ}C$		100	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0 V, V_{GS} = 16 V$			100	nA

## ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 934 \mu A$	1.2		2.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 934 \mu A, \text{ref to } 25^{\circ}C$		-4.9		$mV/^{\circ}C$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10 V, I_D = 27 A$		0.70	0.85	$m\Omega$
		$V_{GS} = 4.5 V, I_D = 27 A$		0.83	1.05	
Forward Transconductance	$g_{FS}$	$V_{DS} = 3 V, I_D = 27 A$		146		S
Gate Resistance	$R_G$	$T_A = 25^{\circ}C$		0.8		$\Omega$

## CHARGES & CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0 V, V_{DS} = 13 V, f = 1 \text{ MHz}$		4360		pF
Output Capacitance	$C_{OSS}$			1150		
Reverse Capacitance	$C_{RSS}$			80		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10 V, V_{DS} = 13 V; I_D = 27 A$		60		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5 V, V_{DS} = 13 V; I_D = 27 A$		26.3		
Threshold Gate Charge	$Q_{G(TH)}$			6.2		
Gate-to-Drain Charge	$Q_{GD}$			4.0		
Gate-to-Source Charge	$Q_{GS}$			10.8		

## SWITCHING CHARACTERISTICS, $V_{GS} = 10 V$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10 V, V_{DD} = 13 V, I_D = 30 A, R_G = 3 \Omega$		10.8		ns
Rise Time	$t_r$			3.4		
Turn-Off Delay Time	$t_{d(OFF)}$			34.7		
Fall Time	$t_f$			5.1		

## SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0 V, I_S = 27 A$	$T_J = 25^{\circ}C$		0.76	1.2	V
			$T_J = 125^{\circ}C$		0.63		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0 V, di/dt = 100 A/\mu s, I_S = 27 A$		45		ns	
Reverse Recovery Charge	$Q_{RR}$			40		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

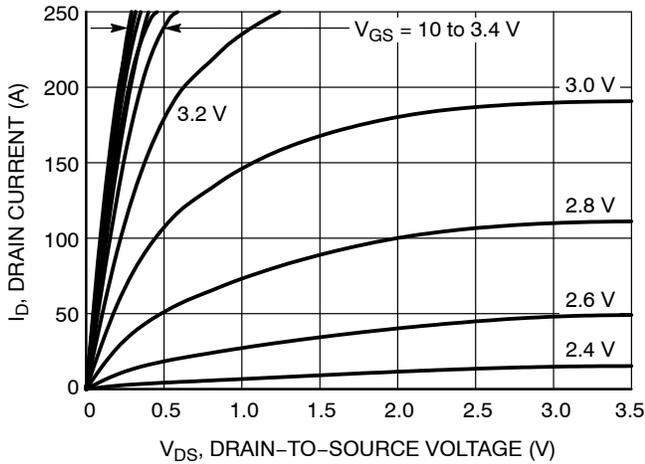


Figure 1. On-Region Characteristics

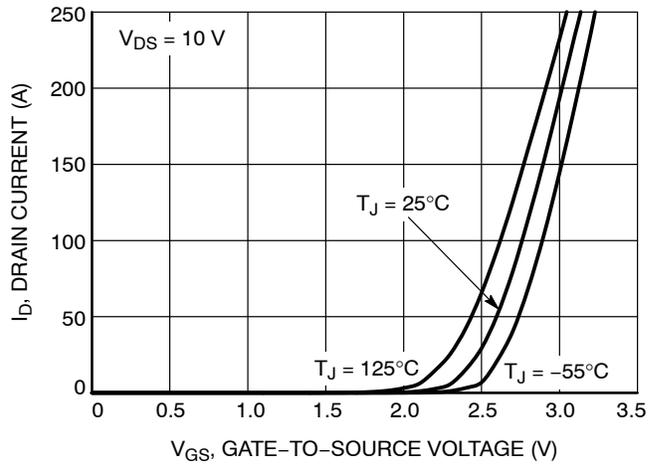


Figure 2. Transfer Characteristics

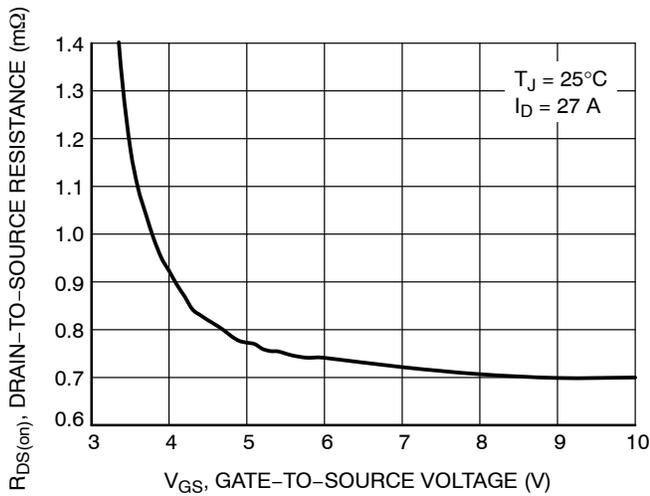


Figure 3. On-Resistance vs. Gate-to-Source Voltage

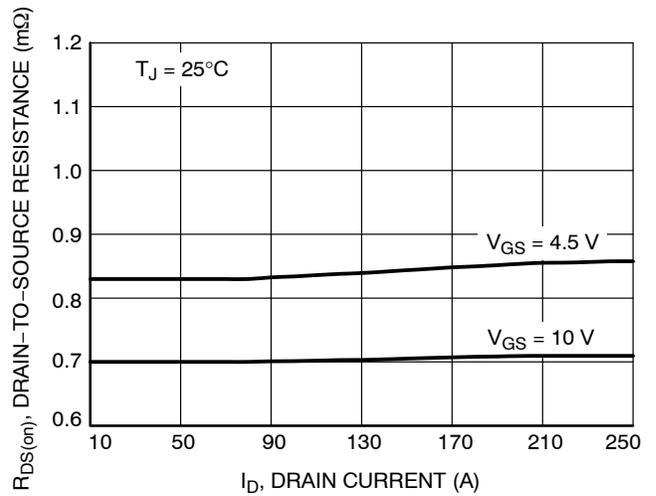


Figure 4. On-Resistance vs. Drain Current

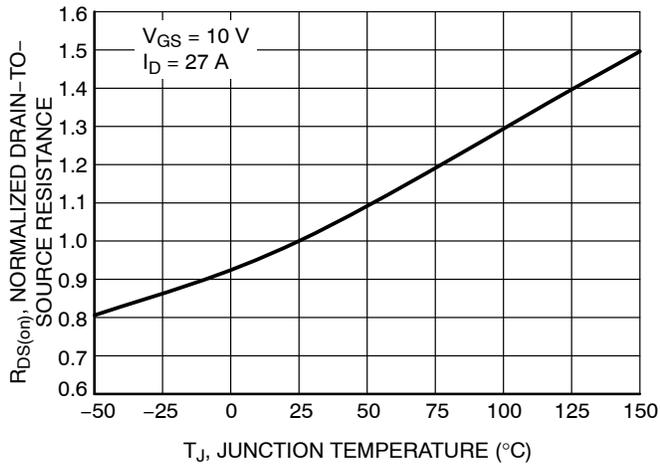


Figure 5. On-Resistance Variation with Temperature

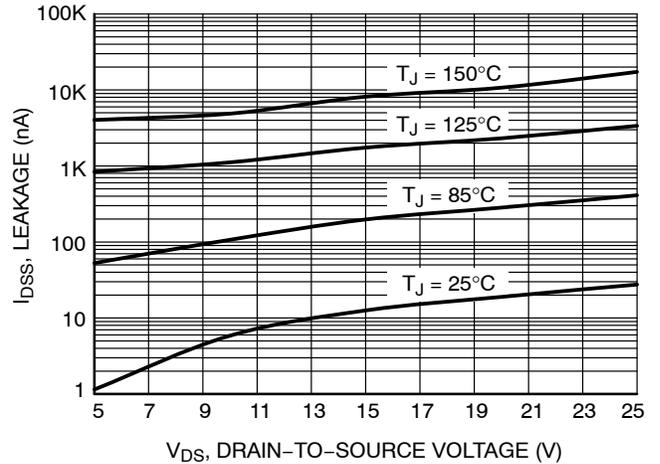


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

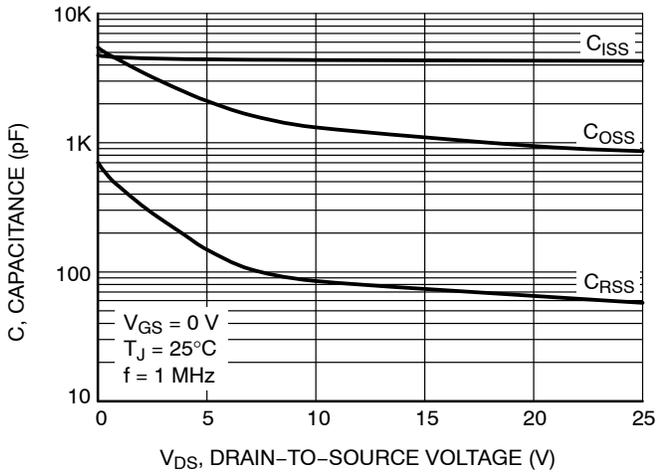


Figure 7. Capacitance Variation

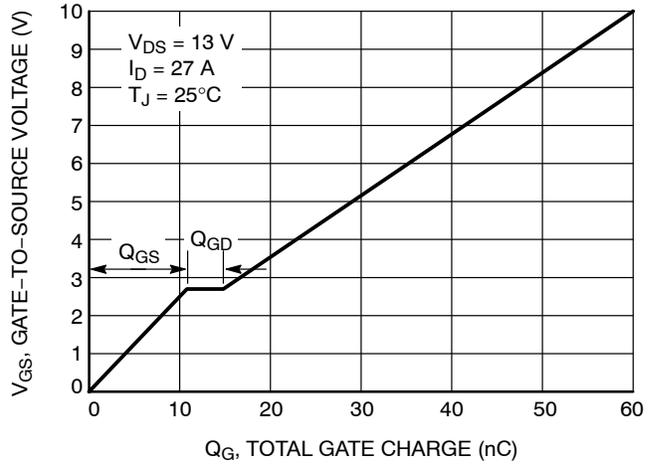


Figure 8. Gate-to-Source Voltage vs. Total Charge

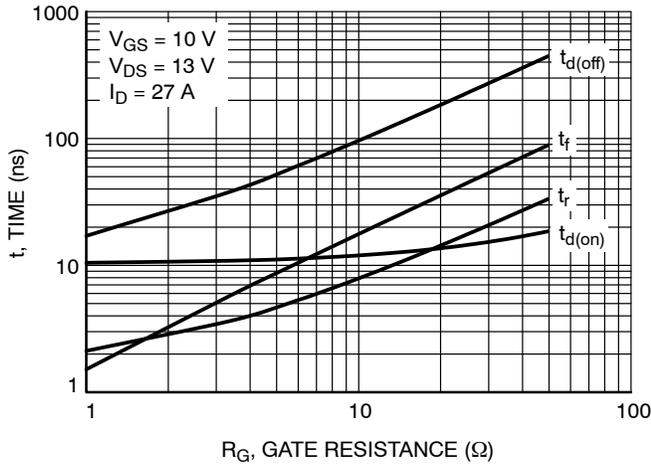


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

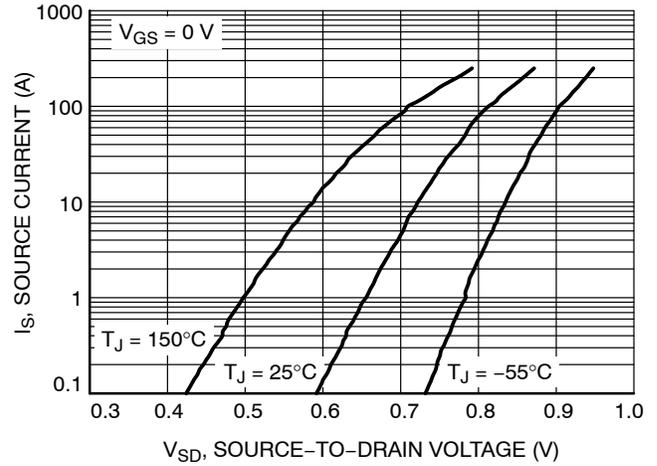


Figure 10. Diode Forward Voltage vs. Current

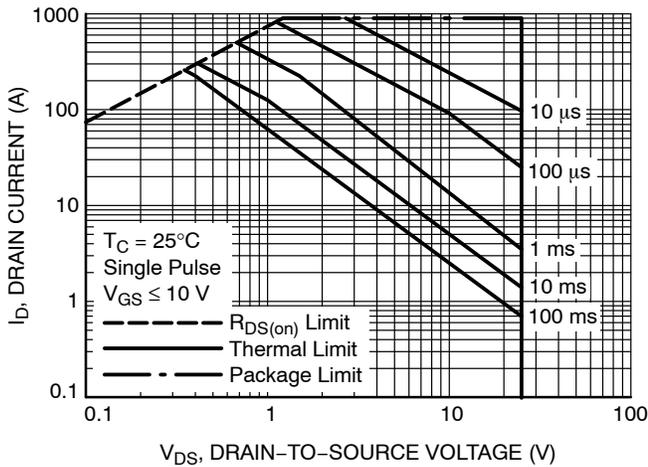


Figure 11. Maximum Rated Forward Biased Safe Operating Area

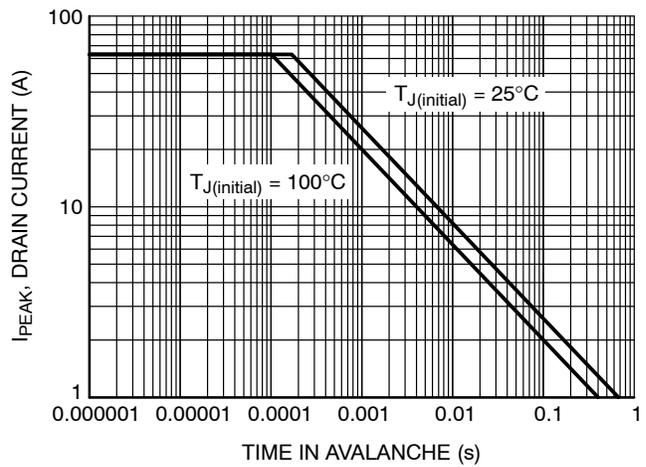


Figure 12. Maximum Drain Current vs. Time in Avalanche

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## TYPICAL CHARACTERISTICS

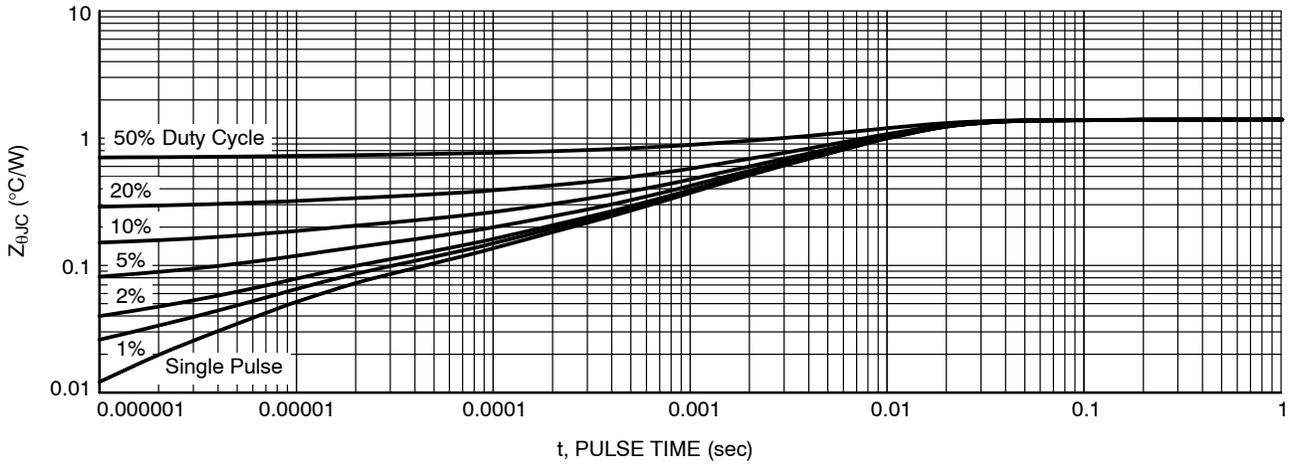


Figure 13. Junction-to-Case Transient Thermal Response

### ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NTTFSS1D1N02P1E	1D1N2	WDFN9 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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